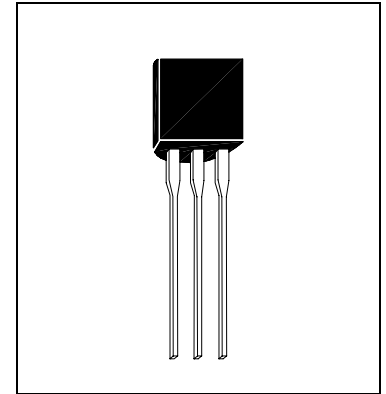




2SA1015

PNP EPITAXIAL PLANAR TRANSISTOR



Description

The 2SA1015 is designed for use in driver stage of AF amplifier and general purpose amplification.

Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature -55~+150°C
Junction Temperature +150°C Maximum
- Maximum Power Dissipation
Total Power Dissipation (Ta=25°C) 400 mW
- Maximum Voltages and Currents (Ta=25°C)
VCBO Collector to Base Voltage 50 V
VCEO Collector to Emitter Voltage 50 V
VEBO Emitter to Base Voltage 5 V
IC Collector Current 150 mA

Characteristics (Ta=25°C)

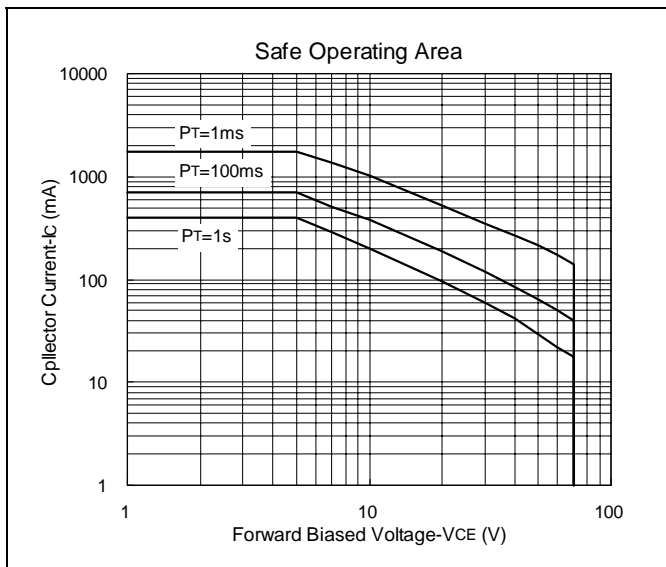
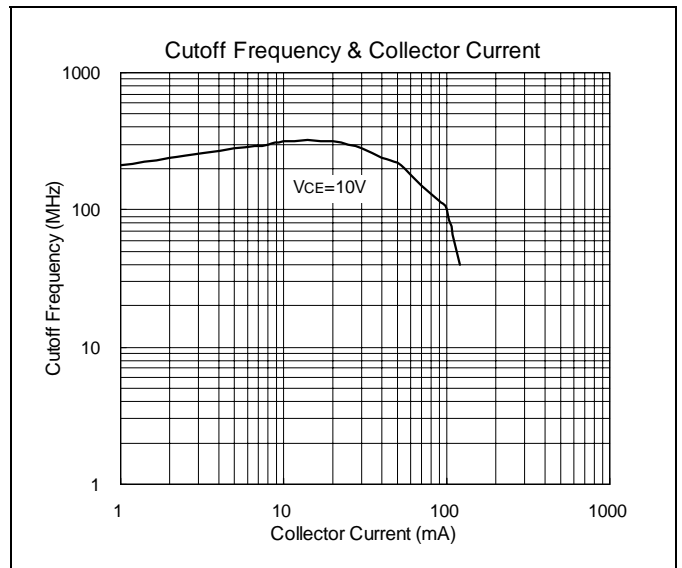
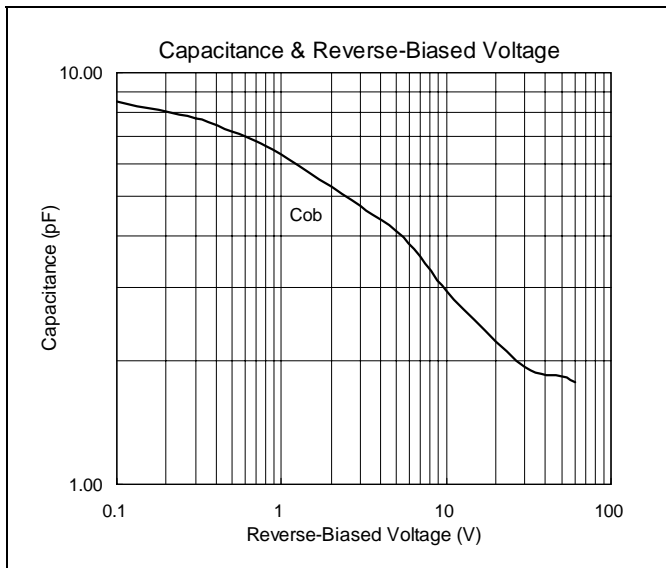
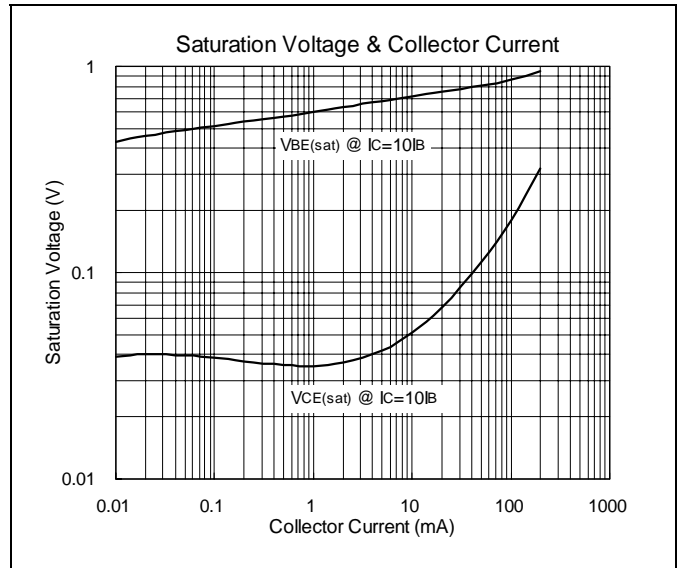
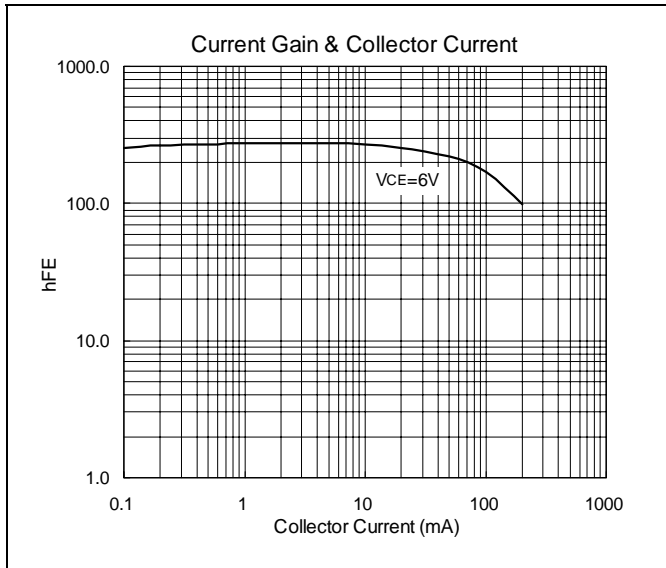
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	50			V	IC=100uA, IE=0
BVCEO	50			V	IC=1mA, IB=0
BVEBO	5			V	IE=10uA, IC=0
ICBO			100	nA	VCB=50V, IE=0
IEBO			100	nA	VEB=5V, IC=0
VCE(sat)			300	mV	IC=100mA, IB=10mA
VBE(sat)			1.1	V	IC=100mA, IB=10mA
hFE1	120		700		VCE=6V, IC=2mA
hFE2	25				VCE=6V, IC=150mA
fT	80			MHz	VCE=10V, IC=1mA, f=100MHz
Cob			7.0	pF	VCB=10V, f=1MHz, IE=0

Classification Of hFE1

Rank	Y	GR	BL
Range	120-240	200-400	350-700

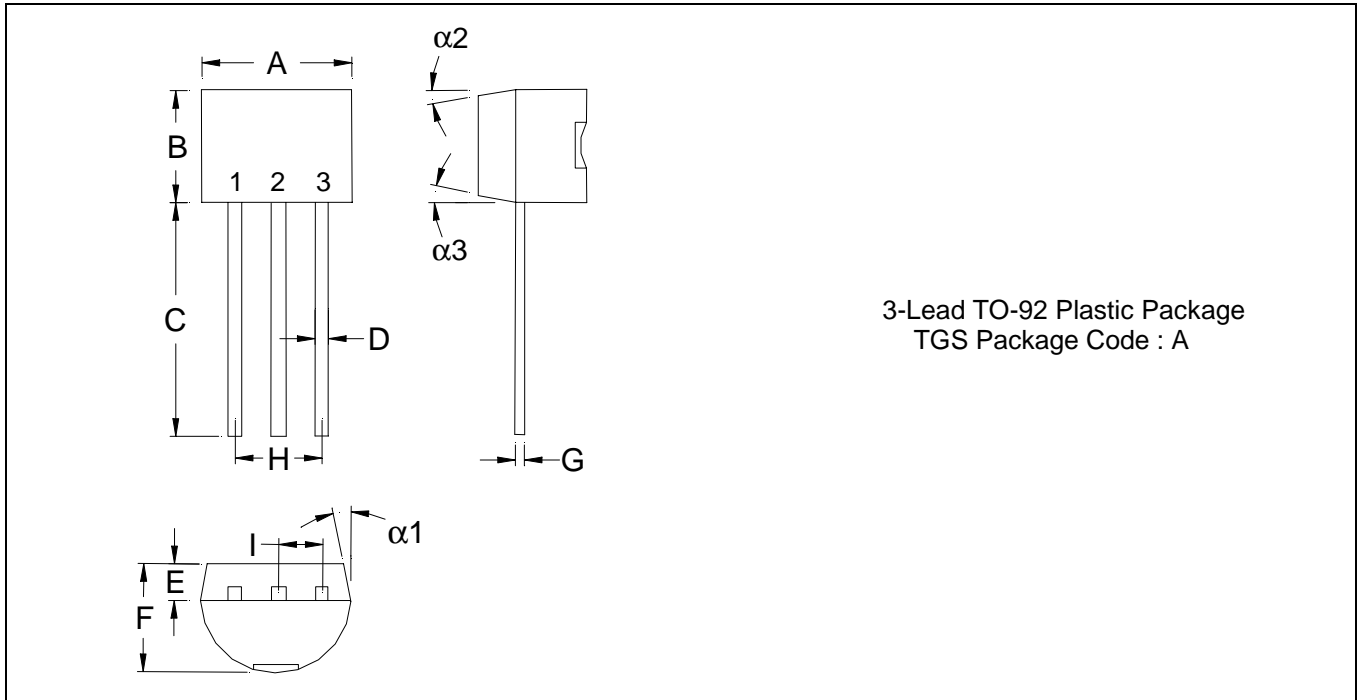


Characteristics Curve





TO-92 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°